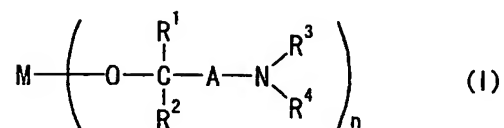


CLAIMS

1. An alkoxide compound represented by general formula (I):



wherein one of R¹ and R² represents an alkyl group having 1 to 4 carbon atoms, and the other represents a hydrogen atom or an alkyl group having 1 to 4 carbon atoms; R³ and R⁴ each represent an alkyl group having 1 to 4 carbon atoms; A represents an alkanediyl group having 1 to 8 carbon atoms; M represents a silicon atom or a hafnium atom; and n represents 4.

2. The alkoxide compound according to claim 1, wherein A in general formula (I) is a methylene group.

3. The alkoxide compound according to claim 1 or 2, wherein M in general formula (I) is a silicon atom.

4. The alkoxide metal compound according to claim 1 or 2, wherein M in general formula (I) is a hafnium atom.

5. A material for thin film formation comprising the alkoxide compound according to any one of claims 1 to 4.

6. A process for thin film formation comprising vaporizing the material for thin film formation according to claim 5, introducing the resulting vapor containing the alkoxide compound, onto a substrate, and causing the vapor to decompose and/or chemically react to form a thin film on the substrate.